

Abstract of the Disclosure

A resist pattern forming method using a coating and developing apparatus and an aligner being connected thereto which are controlled to form a resist film on a surface of a substrate with a base film and a base pattern formed thereon, followed by inspecting at least one of a plurality of measurement items selected from: reflection ratio and film thickness of a base film and a resist film, line width after the development, an accuracy that the base pattern matches with a resist pattern, a defect on the surface after the development, etc. The parameter subject to amendment is selected based on the corresponding data of each of the measurement item such as the film thickness of the resist and the line width after the development, and amendment of the parameters is performed. This results in a reduced workload of an operator, and the appropriate amendment can be performed.